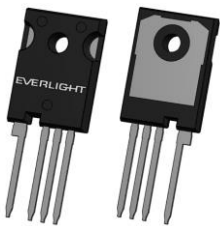


TO-247-4L 1200V N-Channel Enhancement SiC Power MOSFET EL-MAKR02120PA



V_{DS}	=	1200	V
I_D	=	90	A
$R_{DS(on)}$	=	20	mΩ

Features

- High Blocking Voltage with Low On-Resistance
- High Speed Switching with Low Capacitances
- Easy to Parallel and Simple to Drive



Benefits

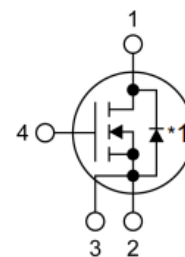
- Improve System Efficiency
- Increase Power Density
- Reduce Heat Sink Requirement
- Reduction of System Cost

Applications

- Solar Inverters
- Switch Mode Power Supply
- Industrial and Motor Inverters
- EV Battery Chargers
- Automotive Traction Inverters
- On Board Chargers
- Pulsed Power applications

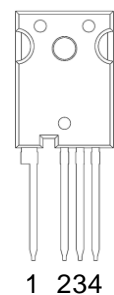
Key Performance Parameters

Schematic



Pin Configuration

1. Drain
 2. Power Source
 3. Driver Source
 4. Gate
- *1. Body Diode



Symbol	V_{DSmin}	V_{GSS}	I_D	I_{DP}	$T_{J,max}$	P_D
Parameter	Drain-Source Voltage	Gate-Source Voltage (DC)	Continuous Drain Current	Pulse Drain Current	Junction temperature	Power Dissipation
Value	1200V	-4~20V	90A	231	175 °C	465W

Maximum Ratings

Parameter	Symbol	Value	Unit	Test Conditions
Drain - Source Voltage	V_{DSmin}	1200	V	$V_{GS}= 0V, I_D= 100\mu A$
Gate - Source Voltage (DC) Max	V_{GS}	-10 / +22	V	
Gate - Source Voltage (DC)	V_{GS}	-4 / +18	V	Recommended operating values
Continuous Drain Current	I_D^{*2}	90	A	
Pulse Drain Current	I_{DP}	231	A	
Power Dissipation	P_D^{*3}	465	W	
Operating Junction	T_J	175	°C	
Storage Temperature	T_{stg}	-55 to +175	°C	
Solder Temperature	T_L	260	°C	
Mounting Torque	M_d	1 8.8	Nm lbf-in	M3 or 6-32 screw

*1 Please be advised not to use SiC-MOSFETs with V_{GS} below 12V as doing so may cause thermal runaway.

*2 Limited by maximum T_a and for Max. R_{thJC}

*3 $P_W \leq 10\mu s$, Duty cycle $\leq 1\%$

*4 Tested after applying V_{GS} for 100ms.

*5 Pulsed

Electrical Characteristics

Parameter	Symbol	Value			Unit	Test Conditions
		Min	Typ	Max		
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	1200	-	-	V	$V_{GS}=0V, I_D=100\mu A$
Gate Threshold Voltage	$V_{GS(th)}$ *4	-	2.8	-	V	$V_{GS}=V_{DS}, I_D=2mA$
Zero Gate Voltage Drain Current	I_{DSS}	-	1	-	μA	$V_{DS}=1200V, V_{GS}=0V$
Gate-Source Leakage Current	I_{GSS+}	-	10	200	nA	$V_{GS}=20V, V_{DS}=0V$
Drain-Source On-State Resistance	$R_{DS(on)}$ *5	-	20	30	m Ω	$V_{GS}=18V, I_D=48A$
			35	50		$V_{GS}=18V, I_D=48A, T_J=175^\circ C$
Input Capacitance	C_{iss}	-	5700	-	pF	$V_{GS}=0V$ $V_{DS}=1000V$ $f=100kHz$
Output Capacitance	C_{oss}	-	190	-		
Reverse Transfer Capacitance	C_{rss}	-	15	-		
Turn-On Delay Time	$t_{d(on)}$	-	50	-	ns	$V_{DS}=800V, I_D=48A$ $L=120\mu H$ $L\sigma=35nH$ $V_{GS}=-4/+18V$ $R_G=2.5\Omega$
Rise Time	t_r	-	20	-		
Turn-Off Delay Time	$t_{d(off)}$	-	45	-		
Fall Time	t_f	-	10	-		
Gate to Source Charge	Q_{gs}	-	83	-	nC	$V_{DS}=800V$ $I_{DS}=48A$ $V_{GS}=-4/18V$
Gate to Drain Charge	Q_{gd}	-	57	-		
Total Gate Charge	Q_g	-	220	-		
Gate resistance	R_G	-	0.9	-	Ω	$f=1MHz, V_{AC}=25mV$

Body Diode Characteristics

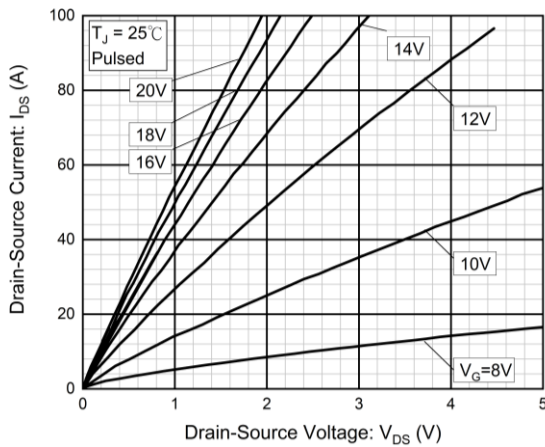
Parameter	Symbol	Value		Unit	Test Conditions
		Typ.	Max.		
Diode Forward Voltage	V_{SD}	4.7	-	V	$V_{GS} = -4V, I_S = 48A$
Continuous Diode Forward Current	I_S	-	60	A	

Thermal Characteristics (Measured conformable to JESD51-14.)

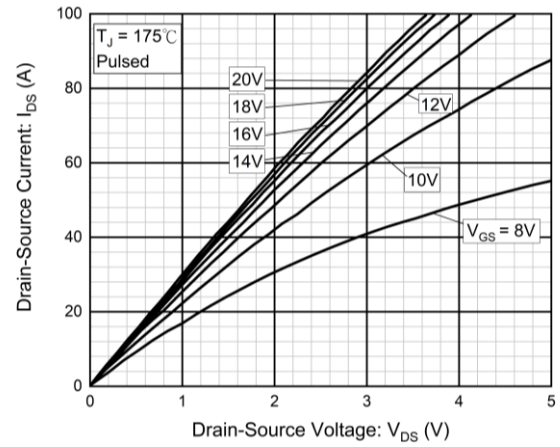
Parameter	Symbol	Value		Unit
		Typ	Max	
Thermal Resistance from Junction to Case	$R_{\theta JC}$	0.20	0.32	$^{\circ}C/W$

Typical Performance

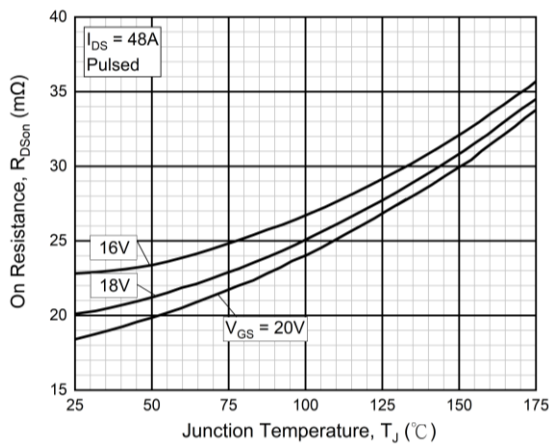
Typical Output Characteristics (I)



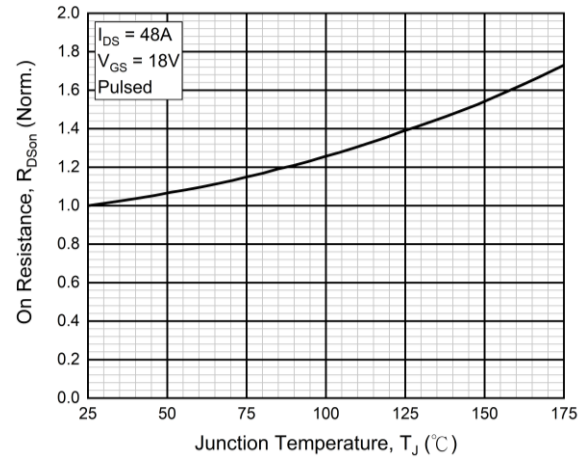
Typical Output Characteristics (II)



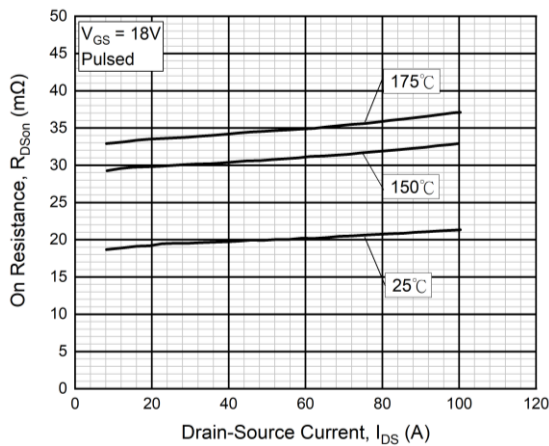
Typical on resistance by various junction temperature and gate voltage



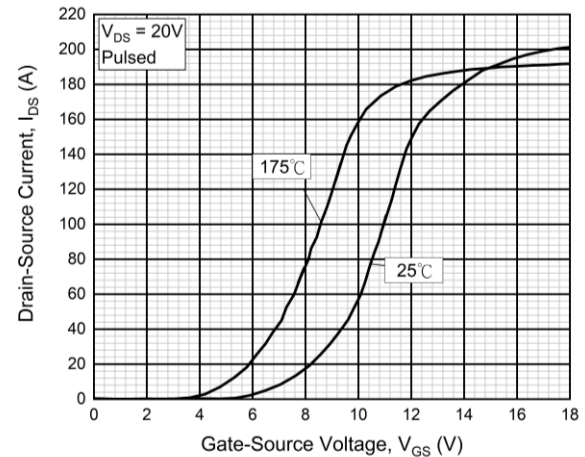
Normalized on resistance by various junction temperature



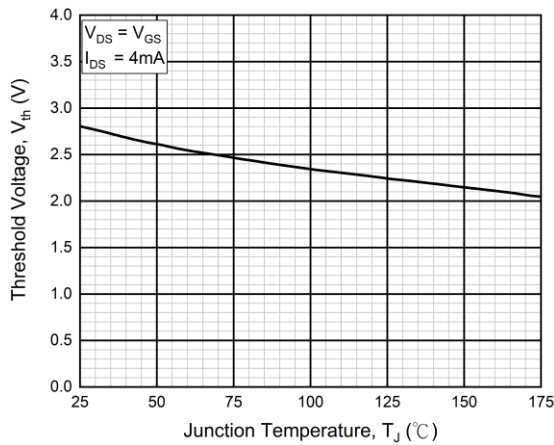
Typical on-resistance by various drain current and junction temperature



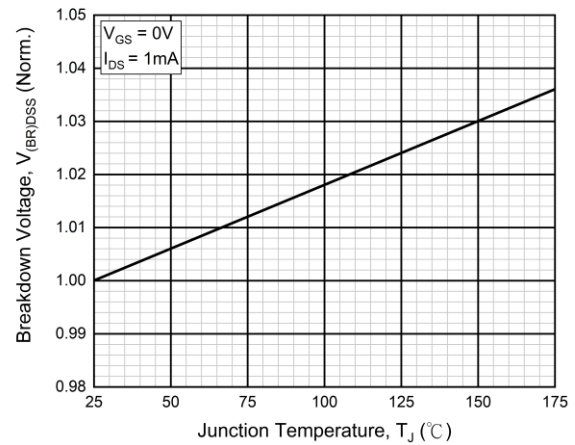
Typical on resistance by various junction temperature and gate voltage



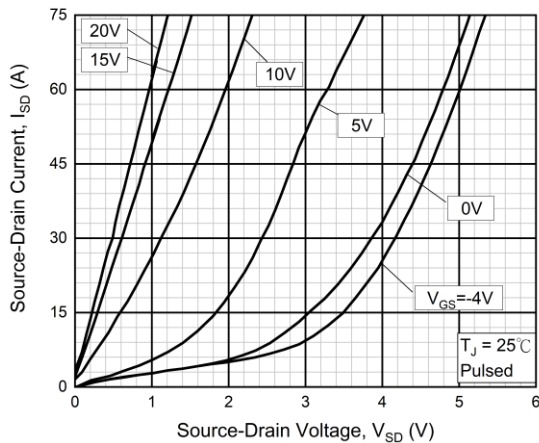
Typical threshold voltage by various junction temperature



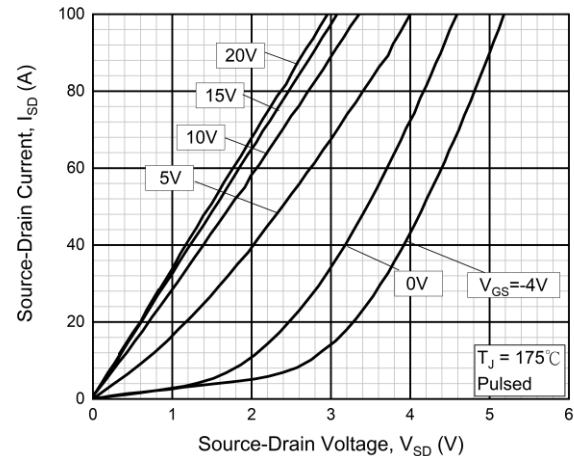
Normalized breakdown voltage by various junction temperature



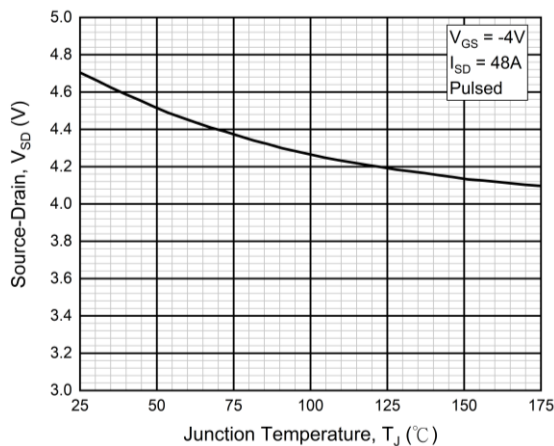
Typical body diode forward current by various forward voltage and gate voltage(I)



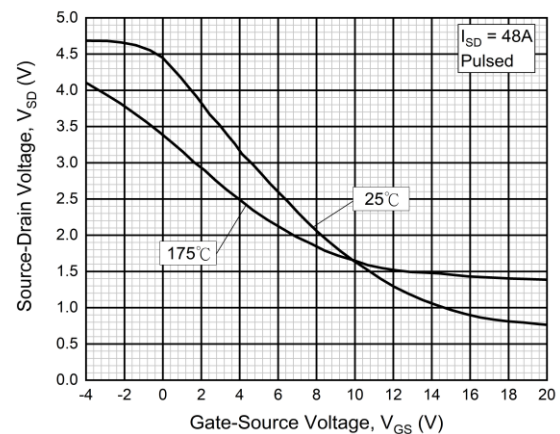
Typical body diode forward current by various forward voltage and gate voltage(II)



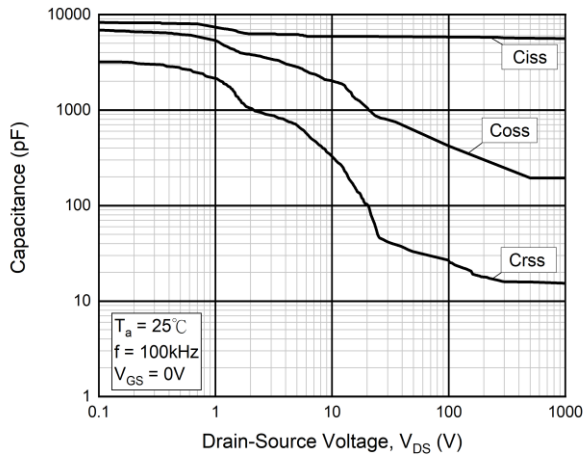
Typical body diode forward voltage by various junction temperature



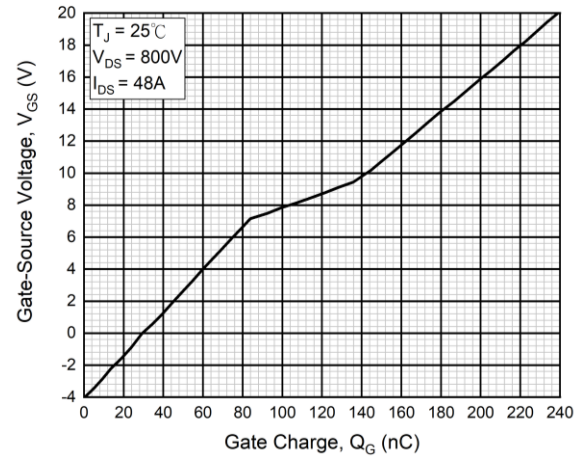
Typical body diode forward voltage by various gate voltage and junction temperature



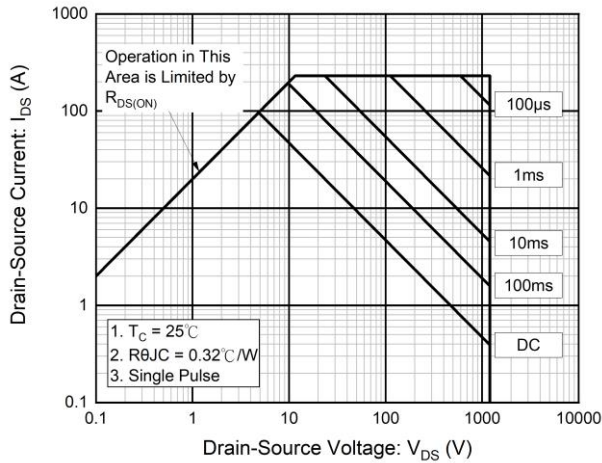
Typical capacitance by various drain voltage



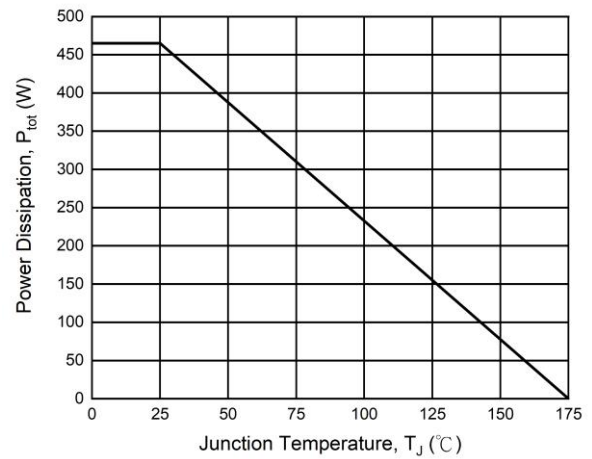
Typical gate charge characteristic



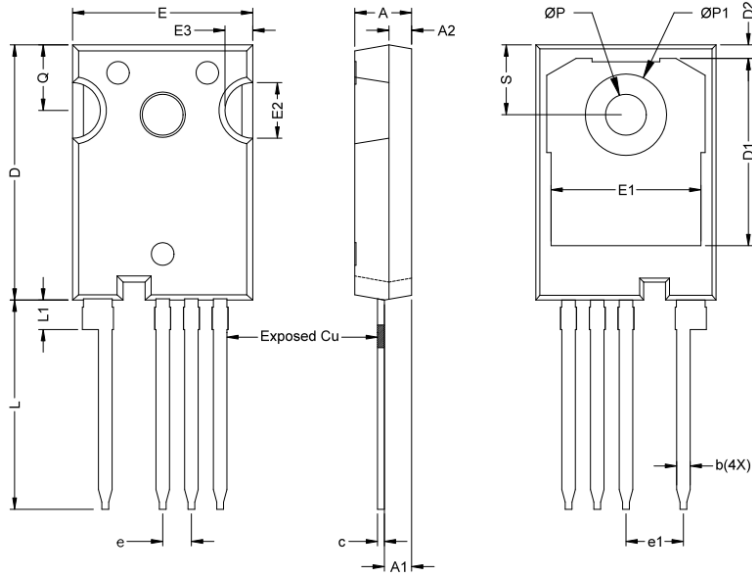
Maximum Safe Operating Area (SOA)



Power dissipation vs. Junction Temperature



Package Outlines

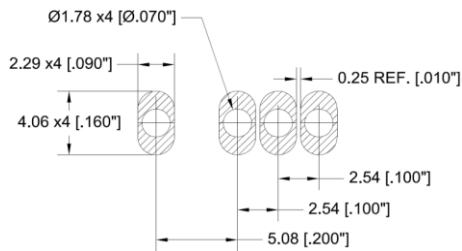


DIM	MILLIMETERS		
	MIN	TYP.	MAX
A	4.82	5.02	5.22
A1	2.21	2.41	2.61
A2	1.8	2	2.2
b	0.95	1.2	1.45
b1	1.95	2.2	2.45
b2	2.95	3.2	3.45
c	0.35	0.6	0.85
D	22.34	22.54	22.74
D1	16.3	16.55	16.8
D2	0.99	1.19	1.39
E	15.74	15.94	16.14
E1	13.01	13.26	13.51
E2	4.71	4.91	5.11
E3	2.26	2.46	2.66
e	2.54 BSC.		
e1	5.08 BSC.		
L	18.23	18.48	18.73
L1	2.35	2.60	2.85
P	3.41	3.61	3.81
P1	6.94	7.19	7.44
Q	5.59	5.79	5.99
S	5.97	6.17	6.37

Unit : mm

Drawing and Dimensions

Recommended pad layout for surface mount leadform



Unit : mm

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